

IS4N46
IS4N45



ISOCOM
COMPONENTS



LOW INPUT CURRENT DARLINGTON OUTPUT OPTICALLY COUPLED ISOLATOR

APPROVALS

- UL recognised, File No. E91231 "JJ"
- 'X' SPECIFICATION APPROVALS
- VDE 0884 in 3 available lead form : -
 - STD
 - G form
 - SMD approved to CECC 00802

DESCRIPTION

The IS4N45, IS4N46 are optically coupled isolators consisting of an infrared light emitting diode and a NPN silicon photo darlington which has an integral base-emitter resistor to optimise switching speed and elevated temperature characteristics in a standard 6pin dual in line plastic package. These devices are designed to equal the 4N45, 4N46 characteristics while providing greater voltage and current capability.

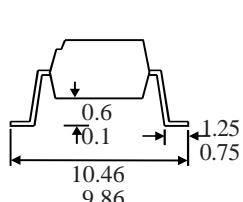
FEATURES

- Options :-
 - 10mm lead spread - add G after part no.
 - Surface mount - add SM after part no.
 - Tape&reel - add SMT&R after part no.
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High Current Transfer Ratio (1500% typ.)
- High BV_{CEO} (55V min.)
- Internal base-emitter resistor minimizes output leakage
- Low input current 0.5mA I_F

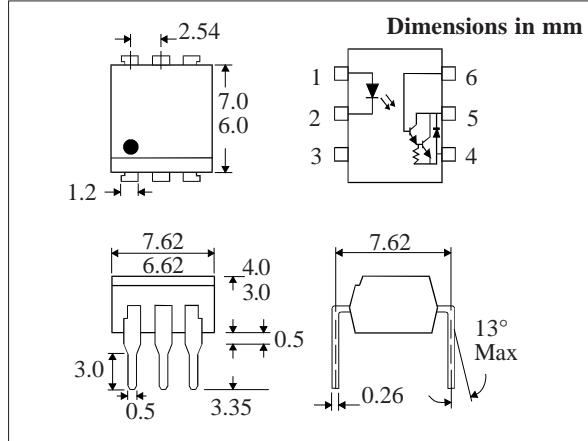
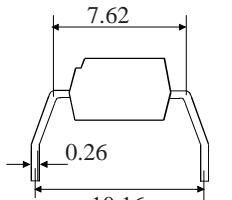
APPLICATIONS

- Telephone ring detector
- Digital logic ground isolation
- Low input current line receiver
- Logic to reed relay interface
- Level shifting
- Interface between logic families
- Line voltage status indicator - low input power dissipation

OPTION SM SURFACE MOUNT



OPTION G



ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature	-40°C to +125°C
Operating Temperature	-25°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage V _{CEO}	55V
Emitter-base Voltage V _{EBO}	6V
Collector Current	150mA
Power Dissipation	300mW

POWER DISSIPATION

Total Power Dissipation	350mW
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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.5	V	$I_F = 10\text{mA}$
	Reverse Current (I_R)			10	μA	$V_R = 4\text{V}$
Output	Collector-emitter Breakdown (BVceo)	55			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown (BVoco)	0.1			V	$I_E = 10\mu\text{A}$
	Emitter-base Breakdown (BVobo)	6			V	$I_E = 10\mu\text{A}$
Coupled	DC Current Transfer Ratio (CTR) IS4N46	350			%	$0.5\text{mA} I_F, 1\text{V} V_{CE}$
	IS4N46	500			%	$1\text{mA} I_F, 1\text{V} V_{CE}$
	IS4N45	250			%	$1\text{mA} I_F, 1\text{V} V_{CE}$
	IS4N46, IS4N45	200			%	$10\text{mA} I_F, 1.2\text{V} V_{CE}$
	Logic Low Output Voltage (V_{OL}) IS4N46		1.0		V	$0.5\text{mA} I_F, 1.75\text{mA} I_{OL}$
	IS4N46		1.0		V	$1\text{mA} I_F, 5\text{mA} I_{OL}$
	IS4N45		1.0		V	$1\text{mA} I_F, 2.5\text{mA} I_{OL}$
	IS4N46, IS4N45		1.2		V	$10\text{mA} I_F, 20\text{mA} I_{OL}$
	Input to Output Isolation Voltage V_{ISO}	5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}	0.6		Ω	$V_{IO} = 500\text{V}$ (note 1)
Input-output Capacitance C_f					pF	$V = 0, f = 1\text{MHz}$
Output rise time, t_r		100	300		μs	$V_{CE} = 2\text{V}, I_C = 20\text{mA}$
Output fall time, t_f		20	100		μs	$R_L = 100\Omega$

